

Emitter common (dual digital transistors)

UMA3N / FMA3A

●Features

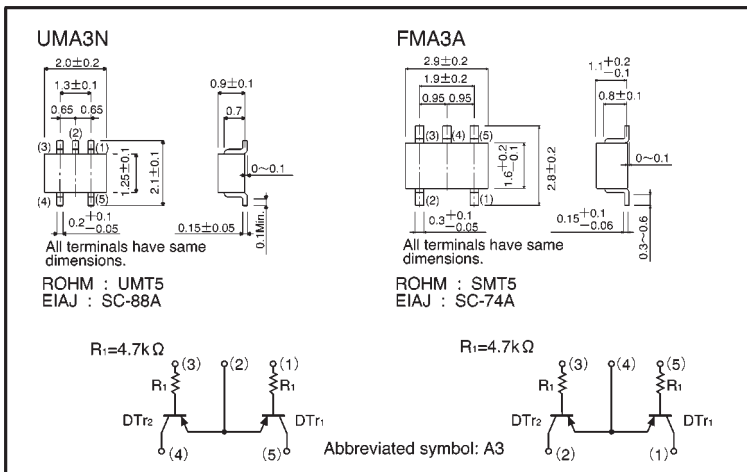
- 1) Two DTA143Ts in a UMT or SMT package.
- 2) Mounting cost and area can be cut in half.

●Structure

Epitaxial planar type PNP silicon transistor (Built-in resistor type)

The following characteristics apply to both DTr₁ and DTr₂.

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		V _{CBO}	−50	V
Collector-emitter voltage		V _{CEO}	−50	V
Emitter-base voltage		V _{EBO}	−5	V
Collector current		I _C	−100	mA
Collector power dissipation	UMA3N	P _C	150 (TOTAL)	mW
	FMA3A		300 (TOTAL)	
Junction temperature		T _j	150	°C
Storage temperature		T _{stg}	−55~+150	°C

*1 120mW per element must not be exceeded.

*2 200mW per element must not be exceeded.

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-50	—	—	V	$I_C = -50\text{ }\mu\text{A}$
Collector-emitter breakdown voltage	BV_{CEO}	-50	—	—	V	$I_C = -1\text{mA}$
Emitter-base break down voltage	BV_{EBO}	-5	—	—	V	$I_E = -50\text{ }\mu\text{A}$
Collector cutoff current	I_{CBO}	—	—	-0.5	μA	$V_{CB} = -50\text{V}$
DC current transfer ratio	h_{FE}	100	250	600	—	$V_{CE}/I_C = -5\text{V}/-1\text{mA}$
Emitter cutoff current	I_{EBO}	—	—	-0.5	μA	$V_{EB} = -4\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.3	V	$I_C/I_E = -5\text{mA}/-0.25\text{mA}$
Transition frequency	f_T	—	250	—	MHz	$V_{CE} = -10\text{mA}$, $I_E = 5\text{mA}$, $f = 100\text{MHz}$ *
Input resistance	R_i	3.29	4.7	6.11	k Ω	—

* Transition frequency of the device

●Packaging specifications

Part No.	Packaging type	Taping	
	Code	TR	T148
	Basic ordering unit (pieces)	3000	3000
UMA3N			—
FMA3A		—	

●Electrical characteristic curves

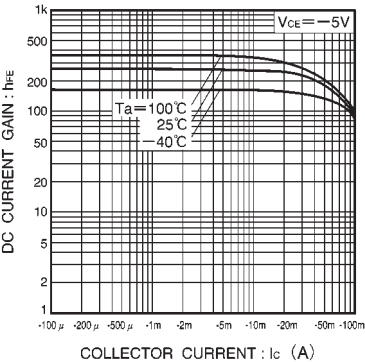


Fig.1 DC current gain vs. collector current

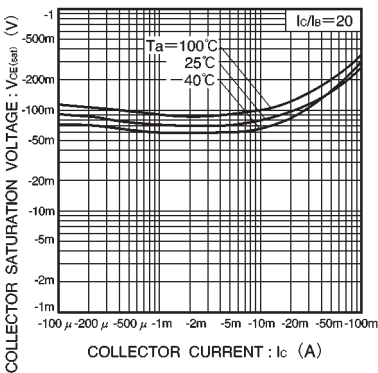


Fig.2 Collector-emitter saturation voltage vs. collector current